



Ultra-Fast Recovery Diodes 8A FRED Pt

Features

- Adopt FRED chip
- Low forward Voltage drop
- Fast reverse recovery time
- High frequency operation
- High purity, high temperature epoxy encapsulation for



MURSL860F

■Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Min	Typ	Max
Instantaneous forward voltage drop per diode	V_{FM}	V	$I_{FM}=8.0A$ @ $T_j=25$	-	1.10	1.3
			$I_{FM}=8.0A$ @ $T_j=150$		0.90	1.1
DC reverse current at rated DC blocking voltage per diode	I_{RRM1}	μA	$V_{RM}=V_{RRM}$ $T_j=25$	-	-	5.0
	I_{RRM2}		$V_{RM}=V_{RRM}$ $T_j=150$	-	-	200
Reverse Recovery Time	T_{rr}	ns	$I_F=0.5A$ $I_{RM}=1A$ $I_{RR}=0.25A$ $T_j=25$	-	32	50
			$T_j=25$	-	80.5	-
			$T_j=125$	-	127.5	-
Peak recovery current	I_{RRM}	A	$T_j=25$	-	5.5	-
			$T_j=125$	-	9.5	-
Reverse recovery charge	Q_{rr}	nC	$T_j=25$	-	226.5	-
			$T_j=125$	-	620.0	-

■Thermal Characteristics $T_j=25$ Unless otherwise specified

PARAMETER		SYMBOL	UNIT	MURSL860F
Thermal Resistance	Between junction and case	$R_{\theta J-C}$	/W	5.0
	Between junction and Air	$R_{\theta J-A}$	/W	50

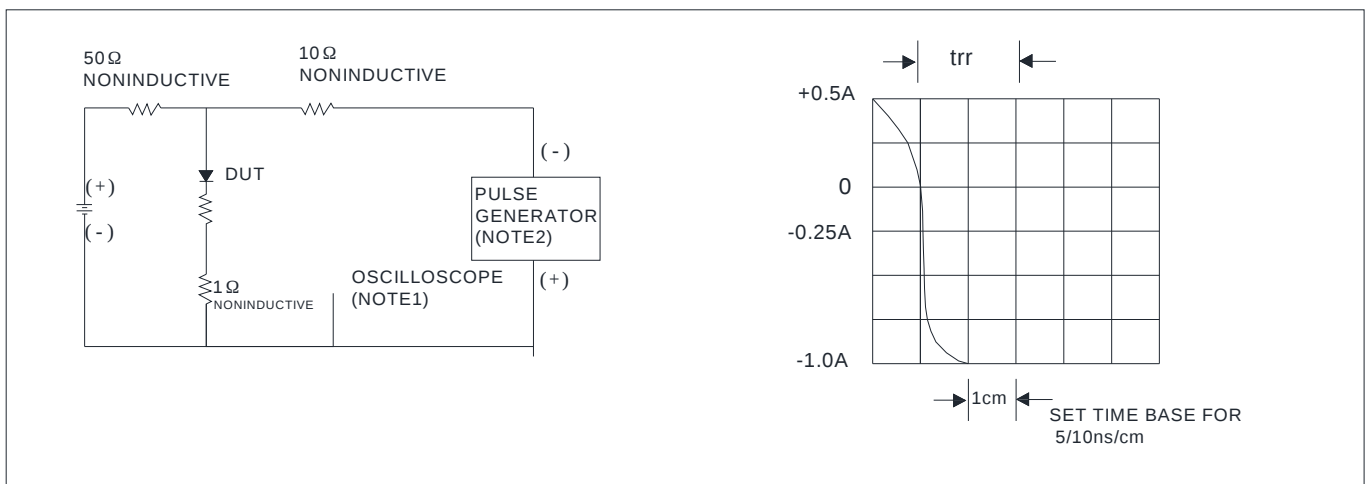
■Ordering Information (Example)

PREFERRED P/N	UNIT WEIGHT(g)	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MURSL860F	Approximate 1.6	50	1000	5000	Tube



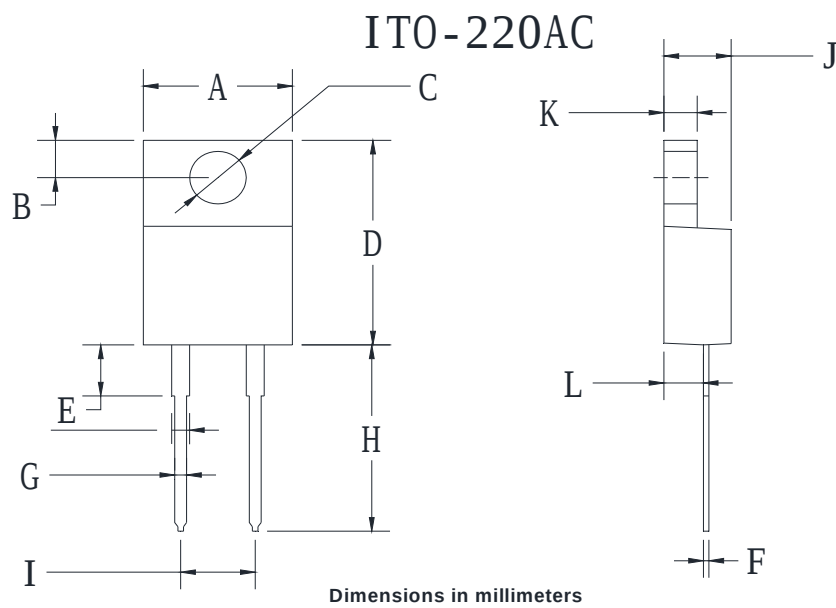
■Characteristics (Typical)

FIG.5: Diagram of circuit and Testing wave form of reverse recovery time





■Outline Dimensions



ITO-220AC		
Dim	Min	Max
A	9.8	10.2
B	2.25	2.75
C	2.95	3.45
D	14.75	15.25
E	3.5	4.1
F	0.45	0.75
G	0.45	0.75
H	13.35	14.15
I	4.97	5.23
J	4.3	4.8
K	2.5	2.74
L	2.58	2.82
M	1.03	1.43



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